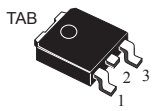
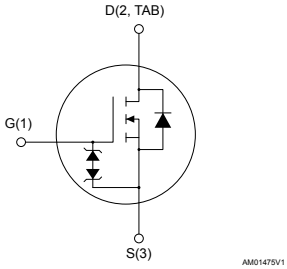
N-channel 600 V, 0.340 Ω typ., 11 A MDmesh™ M2 EP Power MOSFET in a DPAK package



DPAK



Features

Order code	V_{DS} @ T_{Jmax}	$R_{DS(on)}$ max.	I_D
STD15N60M2-EP	650 V	0.378 Ω	11 A

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- Very low turn-off switching losses
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications
- Tailored for very high frequency converters (f > 150 kHz)

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 enhanced performance (EP) technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance, optimized switching characteristics with very low turn-off switching losses, rendering it suitable for the most demanding very high frequency converters.

Product status
STD15N60M2-EP

Product summary	
Order code	STD15N60M2-EP
Marking	15N60M2EP
Package	DPAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_C = 25 °C	11	A
I_D	Drain current (continuous) at T_C = 100 °C	7	A
I_{DM}(1)	Drain current (pulsed)	44	A
P_{TOT}	Total dissipation at T_C = 25 °C	110	W
dv/dt(2)	Peak diode recovery voltage slope	15	V/ns
dv/dt(3)	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_j	Operating junction temperature range		

1. *Pulse width limited by safe operating area.*
2. *I_{SD} ≤ 11 A, di/dt ≤ 400 A/µs, $V_{DS\ peak}$ < $V_{(BR)DSS}$, V_{DD} = 400 V.*
3. *V_{DS} ≤ 480 V*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	1.14	°C/W
$R_{thj\text{-}pcb}$(1)	Thermal resistance junction-pcb	50	°C/W

1. *When mounted on FR-4 board of 1 inch², 2 oz Cu*

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	2.8	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	125	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	600			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V			1	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_C = 125 °C(1)			100	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3.25	4	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 5.5 A		0.340	0.378	Ω

1. *Defined by design, not subject to production test.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS}= 100 V, f = 1 MHz, V_{GS} = 0 V	-	590	-	pF
C_{oss}	Output capacitance		-	30	-	pF
C_{rss}	Reverse transfer capacitance		-	1.1	-	pF
$C_{oss\ eq.}$(1)	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	148	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	7	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 11 A, V_{GS} = 0 to 10 V (see Figure 15. Test circuit for gate charge behavior)	-	17	-	nC
Q_{gs}	Gate-source charge		-	3.1	-	nC
Q_{gd}	Gate-drain charge		-	7.3	-	nC

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.*

Table 6. Switching energy

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{(off)}$	Turn-off energy (from 90% V_{GS} to 0% I_D)	V_{DD} = 400 V, I_D = 1.5 A, R_G = 4.7 Ω, V_{GS} = 10 V	-	4.7	-	µJ
		V_{DD} = 400 V, I_D = 3.5 A, R_G = 4.7 Ω, V_{GS} = 10 V	-	5.2	-	µJ

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 5.5 A,	-	11	-	ns
t_r	Rise time	R_G = 4.7 Ω, V_{GS} = 10 V	-	10	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 14. Test circuit for resistive load switching times and	-	40	-	ns
t_f	Fall time	Figure 19. Switching time waveform)	-	15	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		11	A
I_{SDM}(1)	Source-drain current (pulsed)		-		44	A
V_{SD}(2)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 11 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 11 A, di/dt = 100 A/µs,	-	280		ns
Q_{rr}	Reverse recovery charge	V_{DD} = 60 V	-	2.7		µC
I_{RRM}	Reverse recovery current	(see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	19.5		A
t_{rr}	Reverse recovery time	I_{SD} = 11 A, di/dt = 100 A/µs,	-	400		ns
Q_{rr}	Reverse recovery charge	V_{DD} = 60 V, T_j = 150 °C	-	3.8		µC
I_{RRM}	Reverse recovery current	(see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	19		A

1. *Pulse width is limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

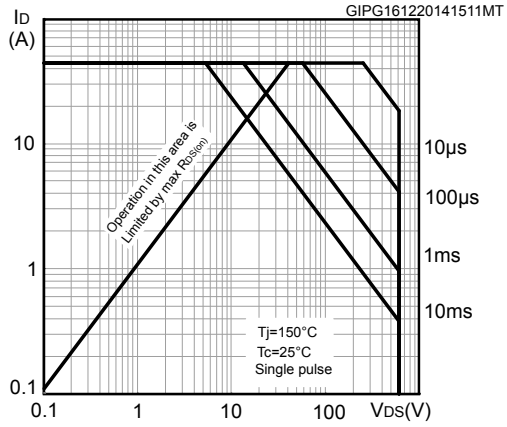


Figure 2. Thermal impedance

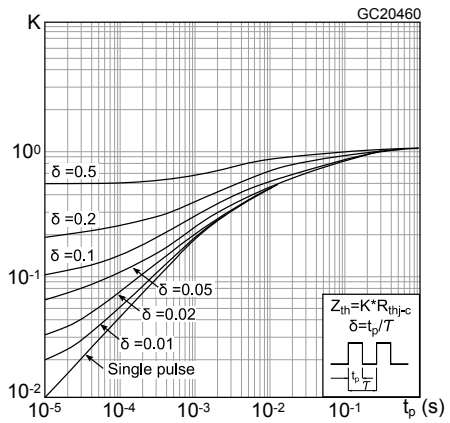


Figure 3. Output characteristics

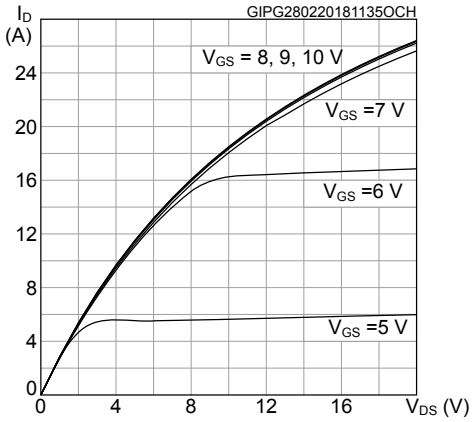


Figure 4. Transfer characteristics

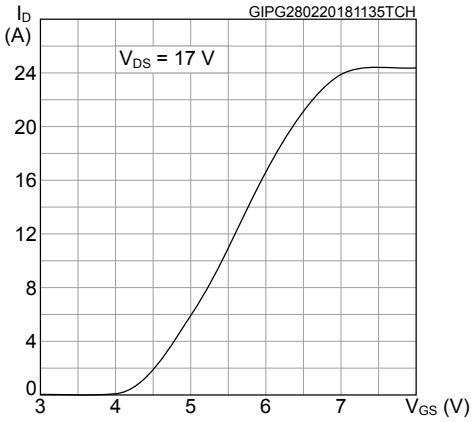


Figure 5. Normalized gate threshold voltage vs temperature

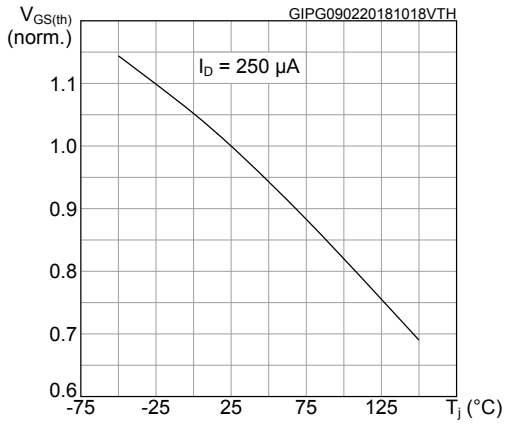


Figure 6. Normalized $V_{(BR)DSS}$ vs temperature

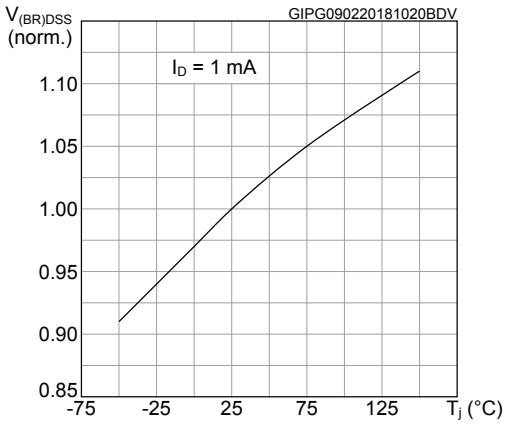


Figure 7. Static drain-source on-resistance

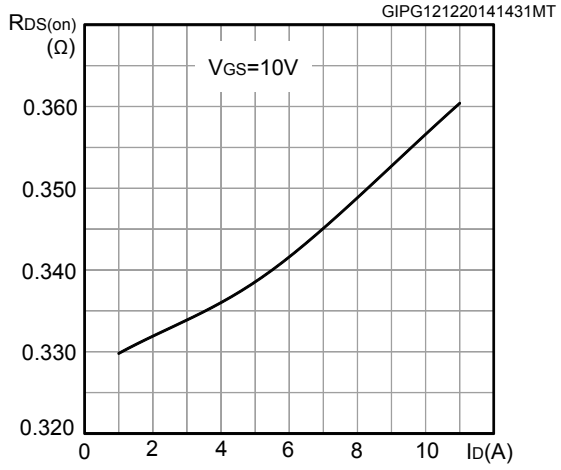


Figure 8. Normalized on-resistance vs temperature

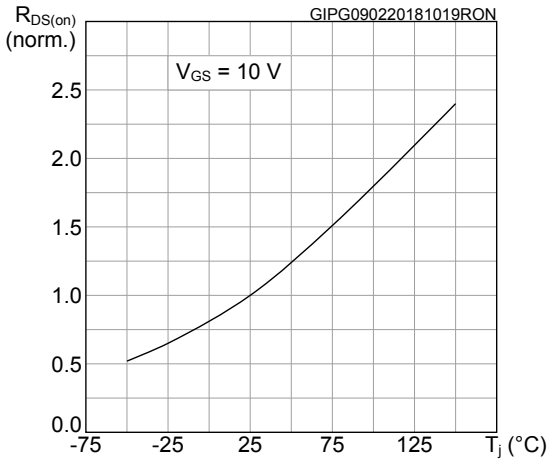


Figure 9. Gate charge vs gate-source voltage

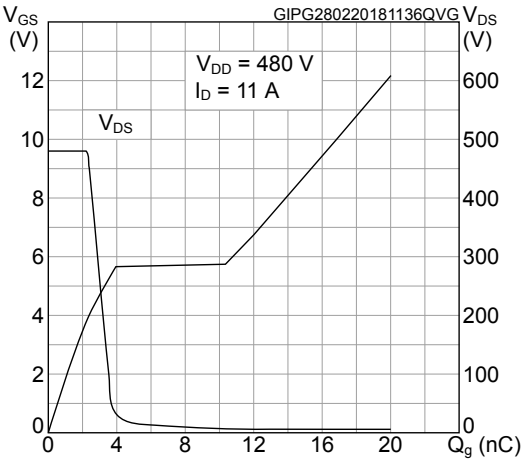


Figure 10. Capacitance variations

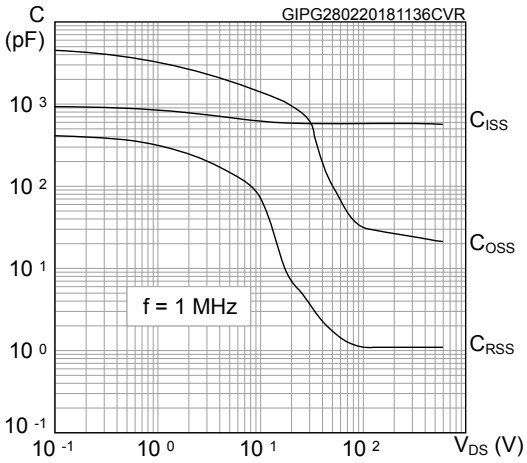


Figure 11. Turn-off switching energy vs drain current

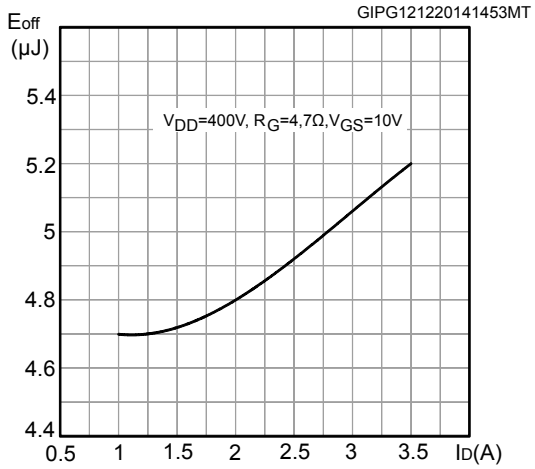


Figure 12. Source-drain diode forward characteristic

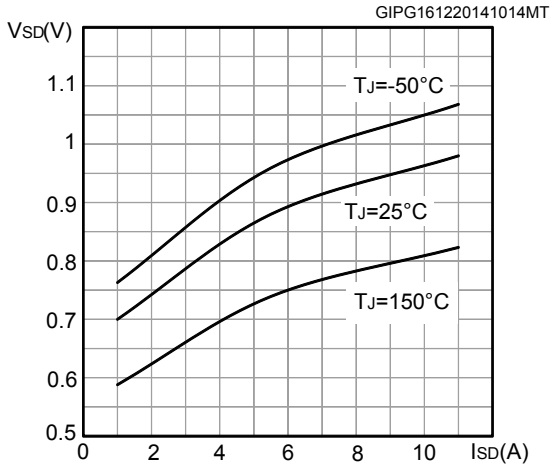
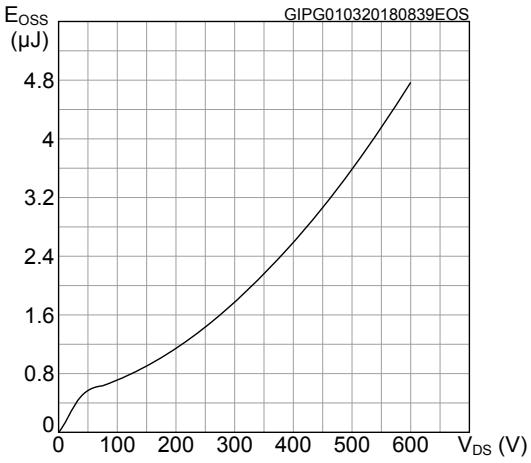


Figure 13. Output capacitance stored energy



3 Test circuits

Figure 14. Test circuit for resistive load switching times

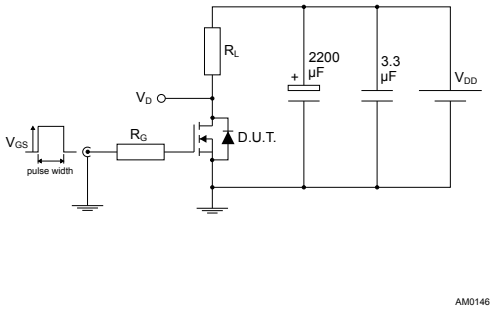


Figure 15. Test circuit for gate charge behavior

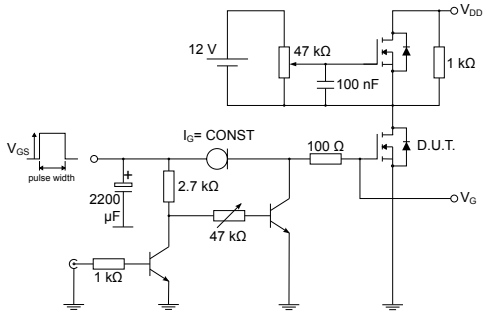


Figure 16. Test circuit for inductive load switching and diode recovery times

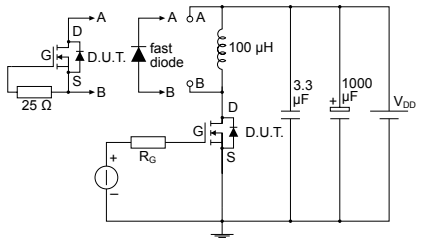


Figure 17. Unclamped inductive load test circuit

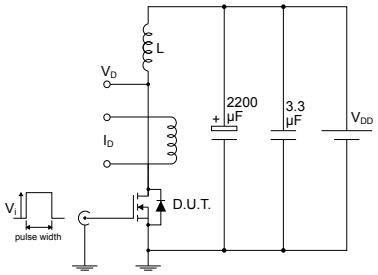


Figure 18. Unclamped inductive waveform

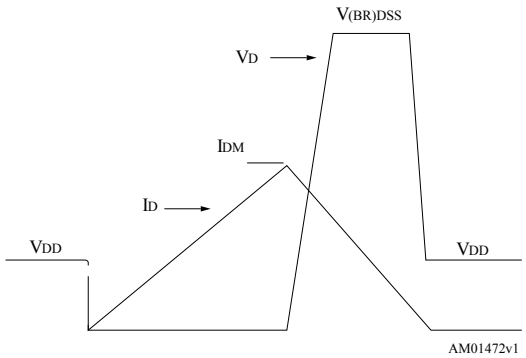
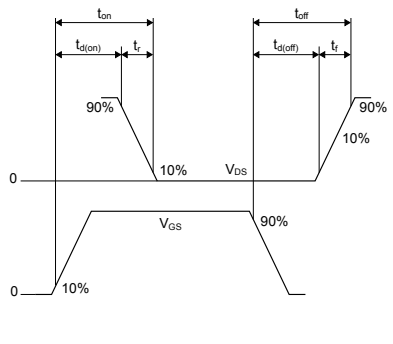


Figure 19. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) type A

Figure 20. **DPAK (TO-252) type A2 package outline**

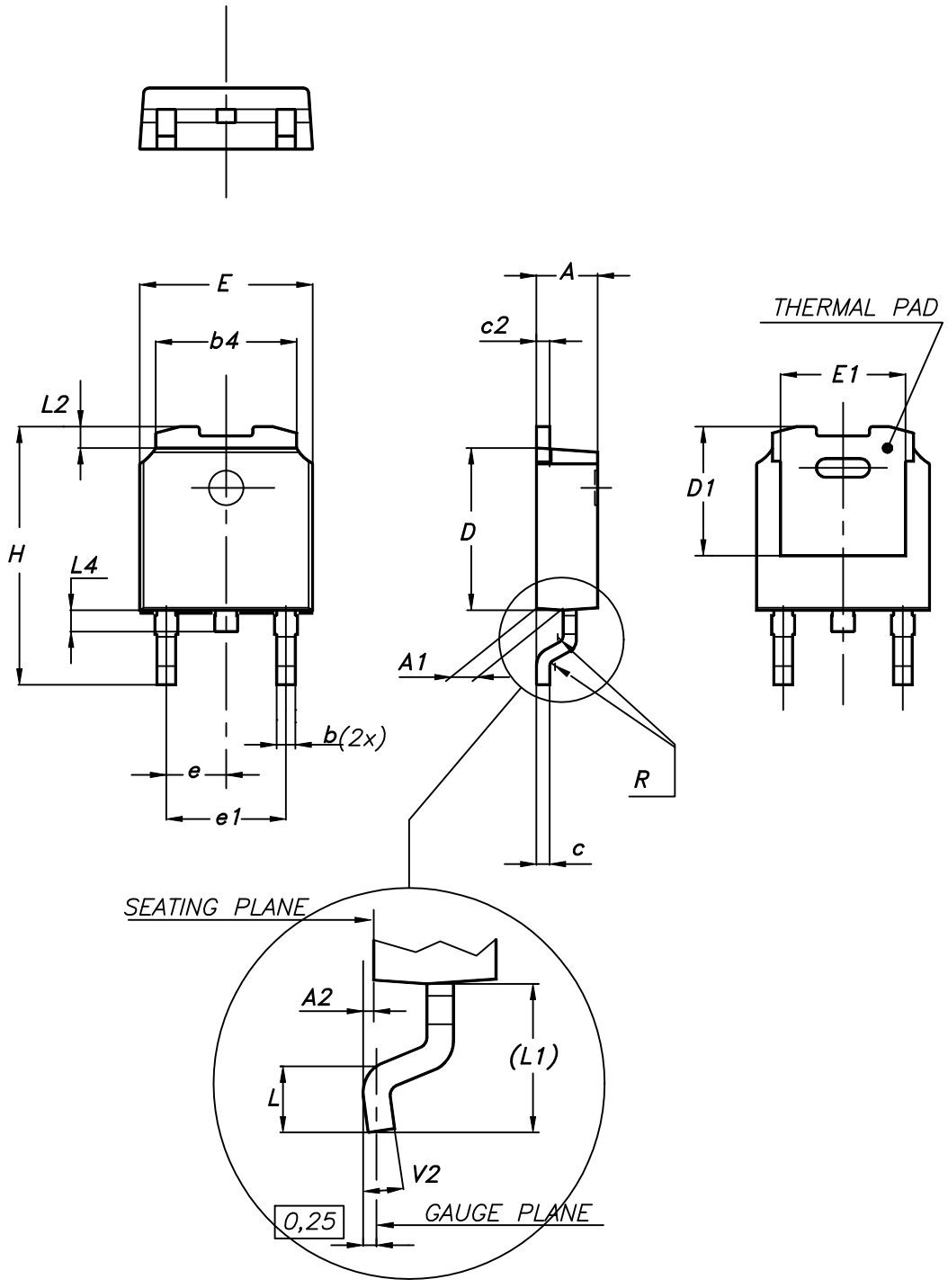
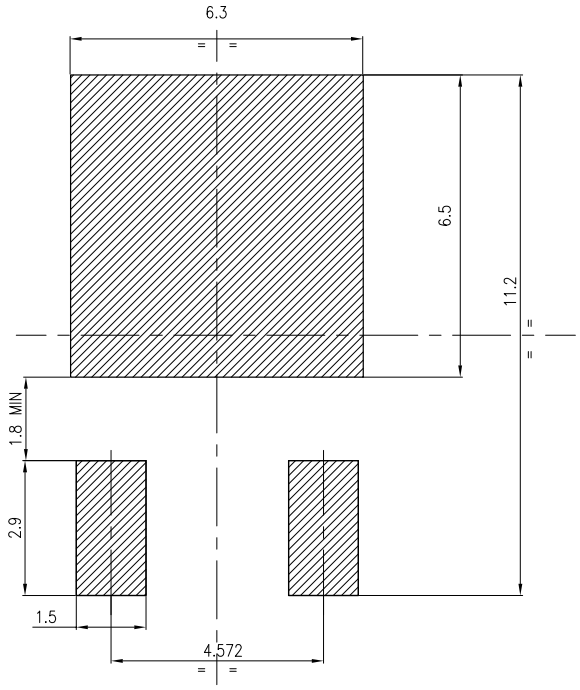


Table 9. **DPAK (TO-252) type A2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 21. **DPAK (TO-252) recommended footprint (dimensions are in mm)**



4.2 DPAK (TO-252) packing information

Figure 22. **DPAK (TO-252) tape outline**

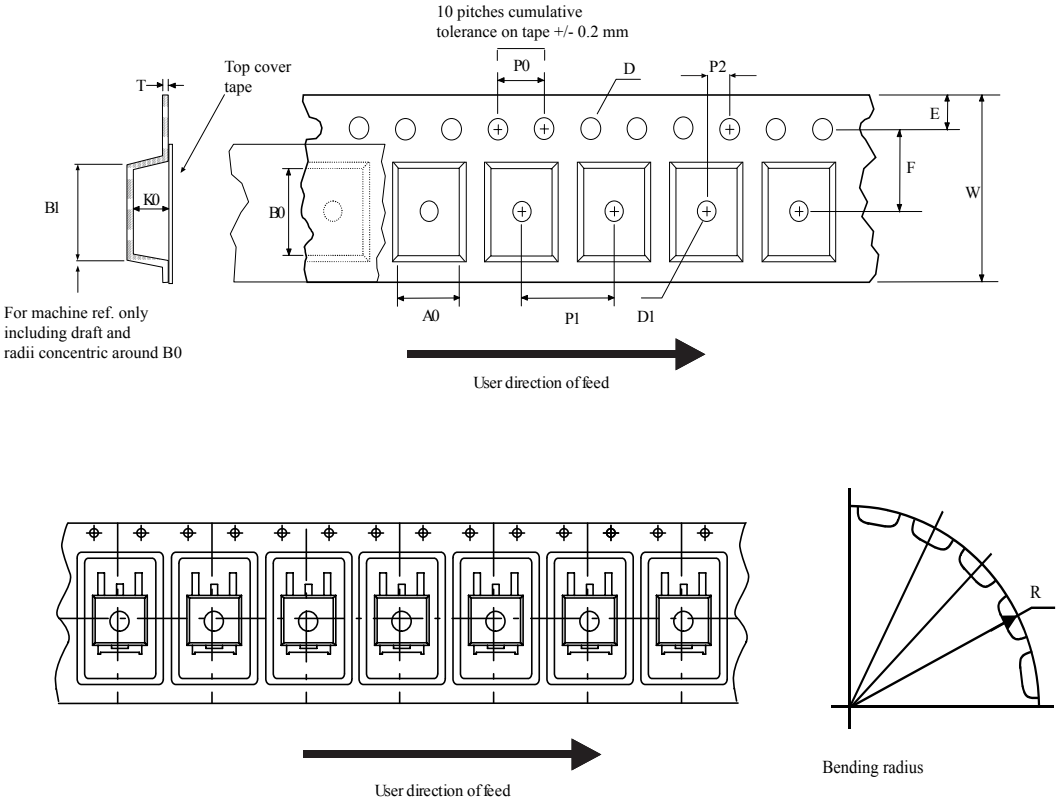


Figure 23. **DPAK (TO-252) reel outline**

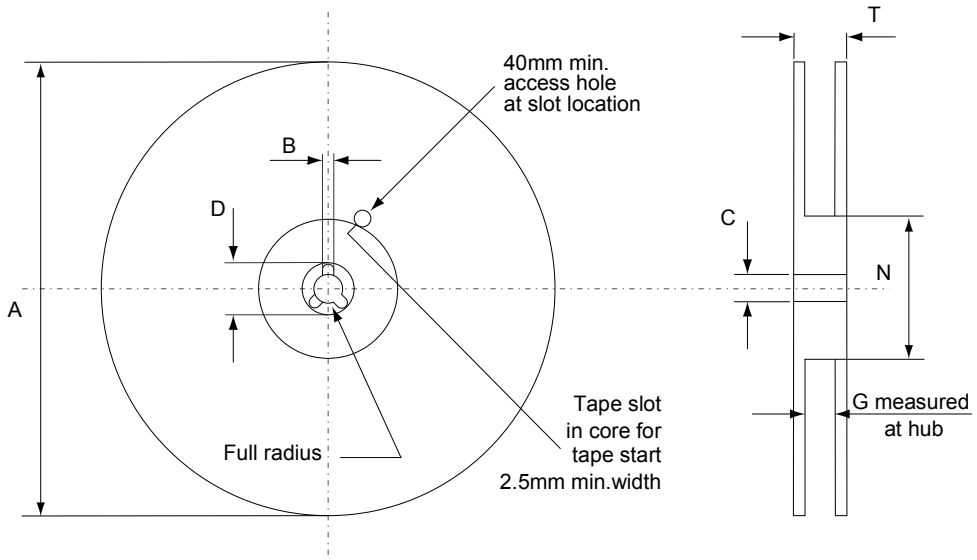


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Table 10. **DPAK (TO-252) tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Revision history

Table 11. **Document revision history**

Date	Revision	Changes
11-May-2015	1	First release.
12-Mar-2018	2	Removed maturity status indication from cover page. The document status is production data. Updated *Section 1 Electrical ratings, Section 2 Electrical characteristics* and *Section 2.1 Electrical characteristics (curves)*. Updated *Section 4.1 DPAK (TO-252) type A2 package information*.
05-Jun-2018	3	Updated Table 1. Absolute maximum ratings, Table 5. Dynamic, Table 6. Switching energy and Table 8. Source drain diode. Updated Figure 1. Safe operating area and Figure 11. Turn-off switching energy vs drain current. Minor text changes

Contents

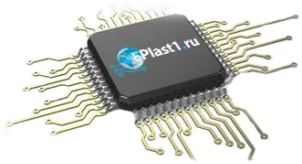
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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